

* Linear time-invariant

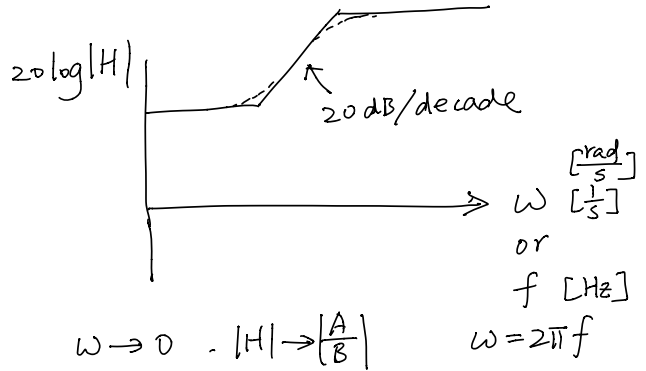
Time response \longleftrightarrow Frequency Response
 Fourier Transform

Phasor $\bar{i}_p \rightarrow I_p e^{j\phi} \quad (= I_p e^{j\omega t + j\phi})$

* Bode Plot

$$H(j\omega) = \frac{A (1 + j\omega\tau_1)}{B (1 + j\omega\tau_2)}$$

Pole $\omega_p = \frac{1}{\tau_2}$
 Zero $\omega_z = \frac{1}{\tau_1}$



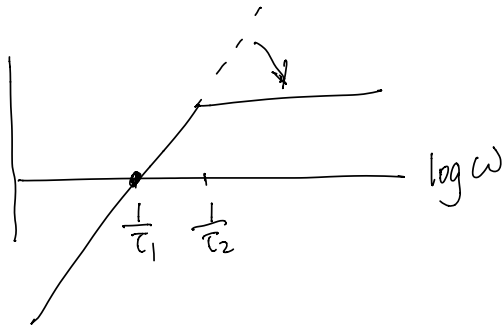
$$H(j\omega) = \frac{(j\omega\tau_1)}{(1 + j\omega\tau_2)}$$

e.g. $\omega_z > \omega_p$

$$\omega_z < \omega < \omega_p, |H| \rightarrow \left| \frac{A}{B} \right| \left| \frac{j\omega\tau_1}{1} \right|$$

$$\omega_p < \omega \quad |H| \rightarrow \left| \frac{A}{B} \right| \left| \frac{j\omega\tau_1}{j\omega\tau_2} \right| = \left| \frac{A}{B} \right| \left| \frac{\tau_1}{\tau_2} \right|$$

$$\omega \rightarrow 0 \cdot H \rightarrow j\omega\tau_1$$



* Ideal Op-amp

* Non-ideal Op-amp

$$A_0 < \infty$$

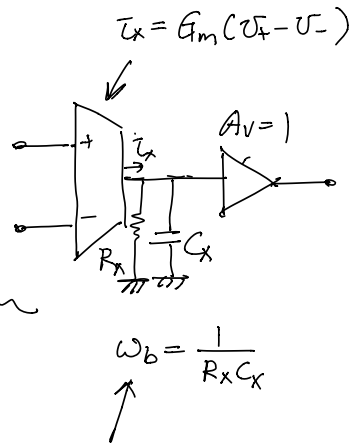
open-loop gain

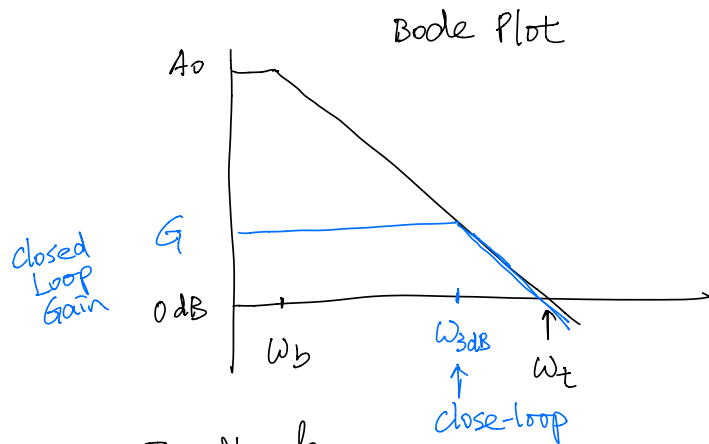
$$\omega_b$$

open-loop 3dB bandwidth

$$\omega_t = A_0 \omega_b$$

unity gain frequency

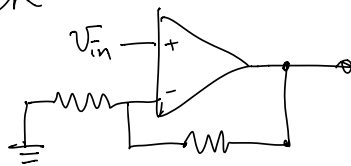




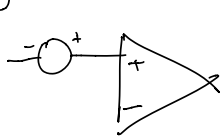
$$A(j\omega) = \frac{A_0}{(1 + j\frac{\omega}{\omega_b})}$$

$$G \cdot \omega_{3dB} = A_0 \omega_b$$

* Feedback



* Offset voltage = Pay attention to polarity



$$A_0(V_+ - V_-)$$

* Slew rate V/μs

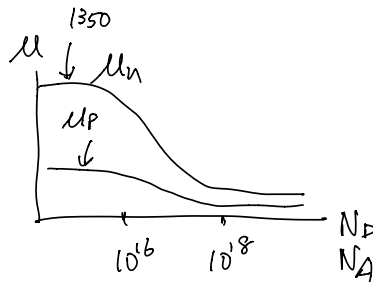
$$V = \mu E$$

$$\frac{\text{cm}}{\text{s}} / \frac{\text{V}}{\text{cm}} = \frac{\text{cm}^2}{\text{s} \cdot \text{V}}$$

* Semiconductor = electron, hole

Drift current

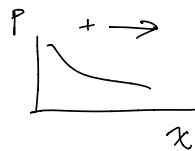
$$\begin{cases} \sigma = nq\mu_n & \text{for n-type} \\ \sigma = pq\mu_p & \text{P-type} \end{cases}$$



Diffusion current

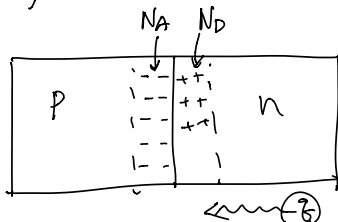
$$J_p = -qD_p \frac{dp}{dx}$$

$$J_n = qD_n \frac{dn}{dx}$$



$$\frac{dp}{dx} < 0$$

* p-n junction → Diode



$$\leftarrow E \text{ (7) } \rightarrow$$

$J_{p,drift} \leftarrow$
 $J_{p,diff} \rightarrow$

} cancel out at equilibrium, i.e. $V_{Bias} = 0$

$J_{n,drift} \leftarrow$
 $J_{n,diff} \rightarrow$

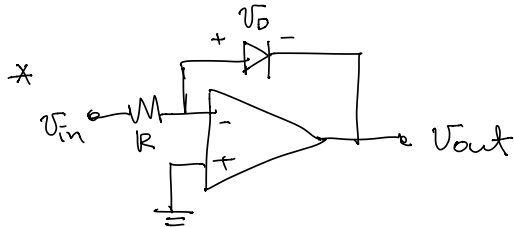
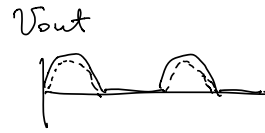
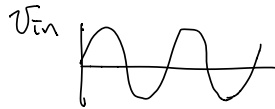
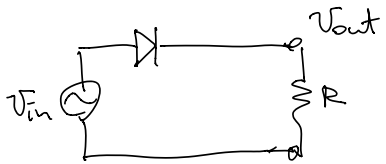
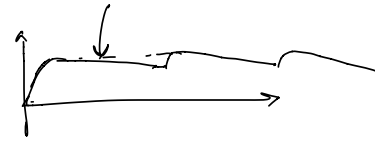
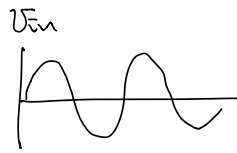
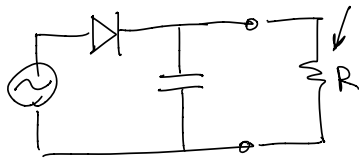
} cancel

Apply V_D

$$I_D = I_S \left(e^{\frac{V_D}{V_T}} - 1 \right) = \text{Large-signal model}$$

* Rectifying circuit

$$\propto (1 - e^{-\frac{t}{RC}})$$



$$V_{out} = V_- - V_D = 0 - V_D = -V_D$$

$$\parallel$$

$$V_T$$

$$\parallel$$

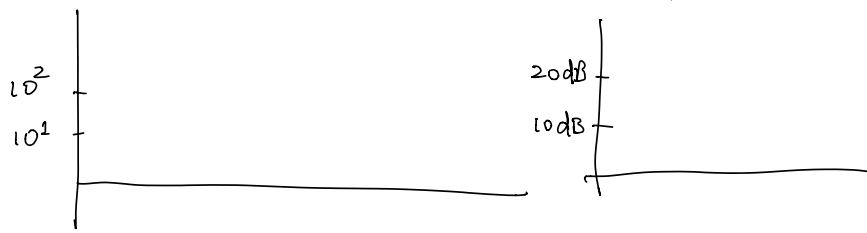
$$0$$

$$I_D = I_S e^{\frac{V_D}{V_T}} = \frac{V_{in} - V_-}{R} = \frac{V_{in}}{R}$$

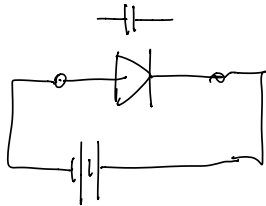
$$V_D = V_T \cdot \ln \frac{V_{in}}{I_S R}$$

$$V_{out} = -V_D = -V_T \ln \frac{V_{in}}{I_S R}$$

$H(j\omega)$



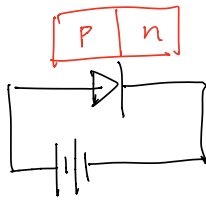
Bode



Reverse bias

$i_D \rightarrow -I_S$

$$C_{dep} = \frac{\epsilon_{Si} A}{W} = \frac{C_0}{\sqrt{1 + \frac{|V_R|}{V_{bi}}}}$$



Forward bias

$i_D = I_S e^{\frac{V_F}{V_T}}$

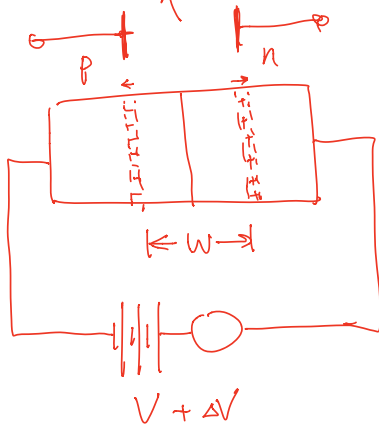
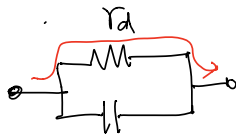
2 capacitance

C_{dep}

C_{diff} (did not discuss)

↑ diffusion cap
= stored minority carriers

Equivalent



$$C_{dep} = \frac{\epsilon_{Si} \cdot A}{W}$$

* Closed Book

2 pages

Calculator →

x 3 decimal
a few %

0.7

0.72

$$i \sim 1.1 \text{ mA}$$

$$1 \text{ mA}$$

$$1.0875$$

↑↑↑

$$1 + \frac{R_2}{R_1}$$

$$\frac{R_2}{R_1} = 100$$

$$e^{\frac{v_B}{V_T}}$$